

Rohit Khanna

List of Publications by Year in descending order

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28
papers

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g-index

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28
docs citations

28
times ranked

483
citing authors

#	ARTICLE	IF	CITATIONS
1	Dry etching of Ga ₂ O ₃ . , 2019, , 263-285.		5
2	Inductively coupled plasma etching of bulk, single-crystal Ga ₂ O ₃ . Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	32
3	Inductively coupled plasma etch damage in (-201) Ga ₂ O ₃ Schottky diodes. Applied Physics Letters, 2017, 110, .	1.5	49
4	Annealing of dry etch damage in metallized and bare (-201) Ga ₂ O ₃ . Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	48
5	Aging and Stability of GaN High Electron Mobility Transistors and Light-Emitting Diodes With TiB_2 - and Ir-Based Contacts. IEEE Transactions on Device and Materials Reliability, 2008, 8, 272-276.	1.5	7
6	Ir-Based Schottky and Ohmic Contacts on n-GaN. Journal of the Electrochemical Society, 2007, 154, H584.	1.3	4
7	Thermal stability of Ohmic contacts to InN. Applied Physics Letters, 2007, 90, 162107.	1.5	7
8	Improved Long-Term Thermal Stability At 350Å°C Of TiB_2 -Based Ohmic Contacts On AlGaN/GaN High Electron Mobility Transistors. Journal of Electronic Materials, 2007, 36, 379-383.	1.0	1
9	Annealing and measurement temperature dependence of W ₂ B ₅ -based rectifying contacts to n-GaN. Applied Surface Science, 2006, 252, 5814-5819.	3.1	9
10	Dry etching of bulk single-crystal ZnO in CH ₄ /H ₂ -based plasma chemistries. Applied Surface Science, 2006, 253, 889-894.	3.1	16
11	Comparison of CH ₄ /H ₂ and C ₂ H ₆ /H ₂ inductively coupled plasma etching of ZnO. Applied Surface Science, 2006, 253, 1269-1273.	3.1	23
12	ZrB ₂ /Pt/Au Ohmic contacts on bulk, single-crystal ZnO. Applied Surface Science, 2006, 253, 2465-2469.	3.1	6
13	Annealing temperature dependence of TiB_2 schottky barrier contacts on n-GaN. Journal of Electronic Materials, 2006, 35, 658-662.	1.0	1
14	Comparison of electrical and reliability performances of TiB_2 -, CrB_2 -, and W_2B_5 -based Ohmic contacts on n-GaN. Journal of Vacuum Science & Technology B, 2006, 24, 744.	1.3	13
15	Improved thermally stable ohmic contacts on p-GaN based on W ₂ B. Applied Physics Letters, 2006, 88, 012104.	1.5	13
16	Thermal stability of W ₂ B and W ₂ B ₅ contacts on ZnO. Applied Surface Science, 2005, 252, 1846-1853.	3.1	9
17	Proton irradiation of ZnO schottky diodes. Journal of Electronic Materials, 2005, 34, 395-398.	1.0	19
18	Properties and annealing stability of Fe doped semi-insulating GaN structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2476-2479.	0.8	12

#	ARTICLE	IF	CITATIONS
19	Changes induced in electrical properties and deep level spectra of p-AlGa _N films by treatment in hydrogen plasma and by proton implantation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 2480-2483.	0.8	1
20	Electrical and optical properties of p-GaN films implanted with transition metal impurities. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 2520-2524.	0.8	3
21	High dose Co-60 gamma irradiation of InGa _N quantum well light-emitting diodes. <i>Applied Physics Letters</i> , 2005, 87, 212107.	1.5	35
22	W2B-based rectifying contacts to n-GaN. <i>Applied Physics Letters</i> , 2005, 87, 052110.	1.5	24
23	W2B based High Thermal Stability Ohmic Contacts to n-GaN. <i>Materials Research Society Symposia Proceedings</i> , 2005, 892, 307.	0.1	0
24	CrB[sub 2] Schottky Barrier Contacts on n-GaN. <i>Journal of the Electrochemical Society</i> , 2005, 152, G804.	1.3	9
25	Improved Thermal Stability CrB2Contacts on ZnO. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 7291-7295.	0.8	3
26	Effects of high-dose 40MeV proton irradiation on the electroluminescent and electrical performance of InGa _N light-emitting diodes. <i>Applied Physics Letters</i> , 2004, 85, 3131-3133.	1.5	32
27	Effects of high dose proton irradiation on the electrical performance of ZnO Schottky diodes. <i>Physica Status Solidi A</i> , 2004, 201, R79-R82.	1.7	12
28	Thermal degradation of electrical properties and morphology of bulk single-crystal ZnO surfaces. <i>Applied Physics Letters</i> , 2004, 85, 3468-3470.	1.5	37